

1. Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

1.3 Applications

- DC-to-DC convertors
- Portable equipment
- Notebook computers
- Switched-mode power supplies

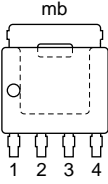
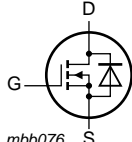
1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 150\text{ °C}$	-	-	30	V
I_D	drain current	$T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1 ; see Figure 3	-	-	63	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	-	62.5	W
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 4.5\text{ V}$; $I_D = 10\text{ A}$; $V_{DS} = 12\text{ V}$; see Figure 10 ; see Figure 11	-	3.2	-	nC
Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; see Figure 8 ; see Figure 9	-	7	9	mΩ

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1,2,3	S	source	 <p>SOT669 (LPAK)</p>	 <p>mbb076</p>
4	G	gate		
mb	D	mounting base; connected to drain		

3. Ordering information

Table 3. Ordering information

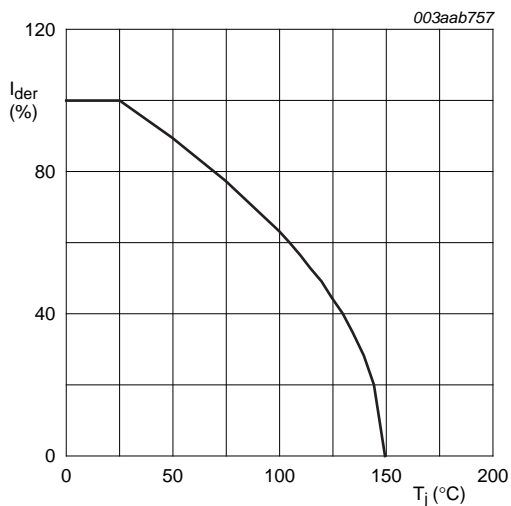
Type number	Package	Description	Version
	Name		
PH9030L	LPAK	Plastic single-ended surface-mounted package (LPAK); 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

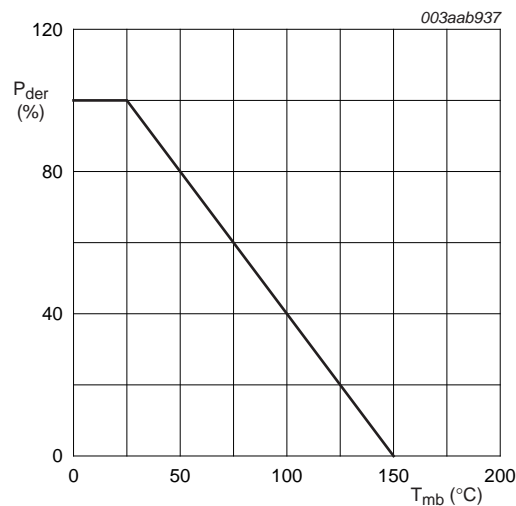
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 150\text{ °C}$	-	30	V
V_{DGR}	drain-gate voltage	$25\text{ °C} \leq T_j \leq 150\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_j = 100\text{ °C}$; see Figure 1	-	39	A
		$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; see Figure 1 ; see Figure 3	-	63	A
I_{DM}	peak drain current	$t_p \leq 10\text{ }\mu\text{s}$; pulsed; $T_{mb} = 25\text{ °C}$; see Figure 3	-	214	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	62.5	W
T_{stg}	storage temperature		-55	150	°C
T_j	junction temperature		-55	150	°C
Source-drain diode					
I_S	source current	$T_{mb} = 25\text{ °C}$	-	52	A
I_{SM}	peak source current	$t_p \leq 10\text{ }\mu\text{s}$; pulsed; $T_{mb} = 25\text{ °C}$	-	208	A
Avalanche Ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; $I_D = 33\text{ A}$; $V_{sup} \leq 30\text{ V}$; unclamped; $t_p = 0.08\text{ ms}$; $R_{GS} = 50\text{ }\Omega$	-	53	mJ



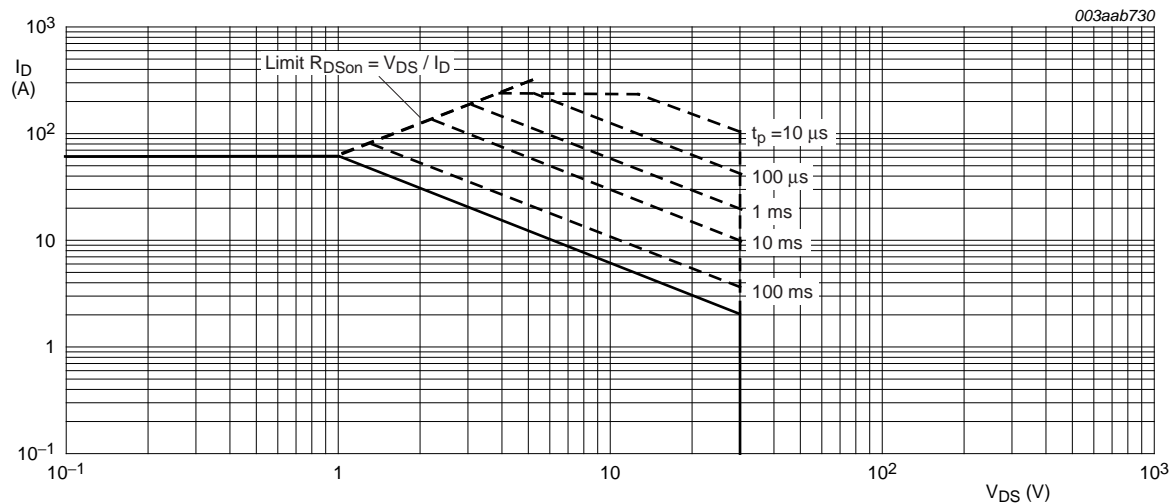
$$I_{der} = \frac{I_D}{I_{D(25^\circ\text{C})}} \times 100\%$$

Fig 1. Normalized continuous drain current as a function of solder point temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of solder point temperature



$T_{mb} = 25^\circ\text{C}; I_{DM}$ is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	2	K/W

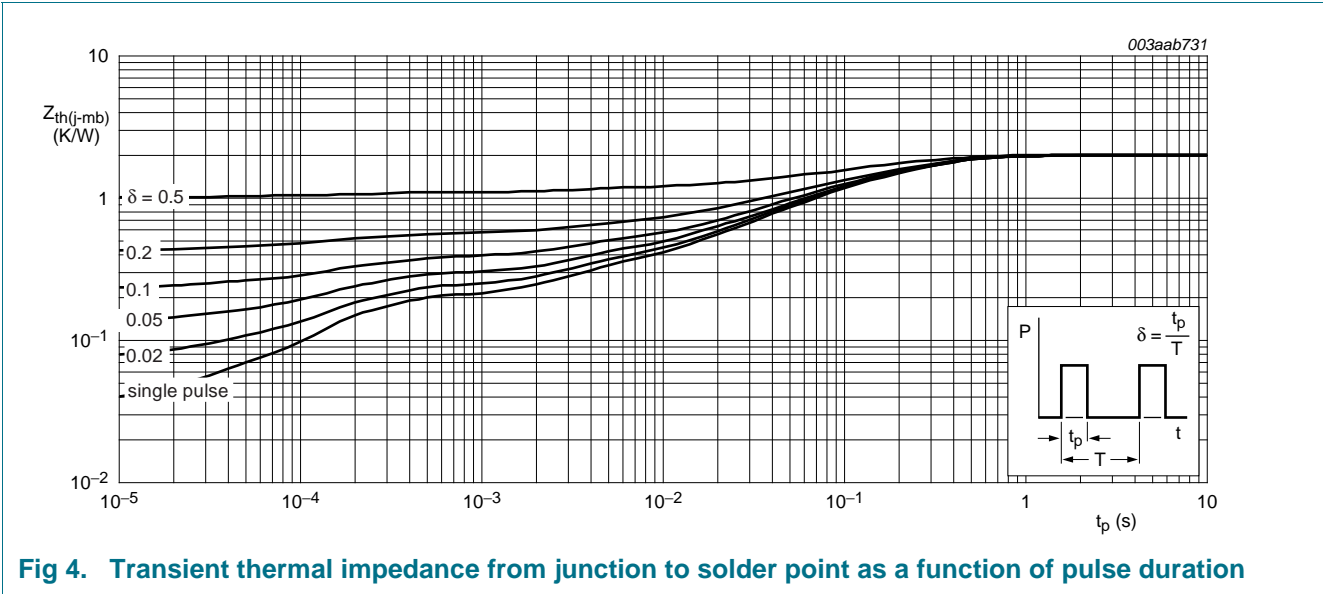


Fig 4. Transient thermal impedance from junction to solder point as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\ \mu A$; $V_{GS} = 0\ V$; $T_j = 25\ ^\circ C$	30	-	-	V
		$I_D = 250\ \mu A$; $V_{GS} = 0\ V$; $T_j = -55\ ^\circ C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\ mA$; $V_{DS} = V_{GS}$; $T_j = 25\ ^\circ C$; see Figure 6 ; see Figure 7	1.3	1.7	2	V
V_{GSth}	gate-source threshold voltage	$I_D = 1\ mA$; $V_{DS} = V_{GS}$; $T_j = -55\ ^\circ C$; see Figure 7 ; see Figure 6	-	-	2.6	V
		$I_D = 1\ mA$; $V_{DS} = V_{GS}$; $T_j = 150\ ^\circ C$; see Figure 7 ; see Figure 6	0.8	-	-	V
I_{DSS}	drain leakage current	$V_{DS} = 30\ V$; $V_{GS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	1	μA
I_{GSS}	gate leakage current	$V_{GS} = 16\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	100	nA
		$V_{GS} = -16\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10\ V$; $I_D = 25\ A$; $T_j = 150\ ^\circ C$; see Figure 8 ; see Figure 9	-	11.9	15.8	m Ω
		$V_{GS} = 4.5\ V$; $I_D = 25\ A$; $T_j = 25\ ^\circ C$; see Figure 8 ; see Figure 9	-	10	12.5	m Ω
		$V_{GS} = 10\ V$; $I_D = 25\ A$; $T_j = 25\ ^\circ C$; see Figure 8 ; see Figure 9	-	7	9	m Ω
I_{DSS}	drain leakage current	$V_{DS} = 30\ V$; $V_{GS} = 0\ V$; $T_j = 150\ ^\circ C$	-	-	100	μA
R_G	internal gate resistance (AC)	$f = 1\ MHz$	-	0.56	-	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 10\ A$; $V_{DS} = 12\ V$; $V_{GS} = 4.5\ V$; see Figure 10 ; see Figure 11	-	13.3	-	nC
Q_{GS}	gate-source charge		-	4.8	-	nC
Q_{GD}	gate-drain charge		-	3.2	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	1.8	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	3	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 10\ A$; $V_{DS} = 12\ V$; see Figure 10 ; see Figure 11	-	2.72	-	V
C_{iss}	input capacitance	$V_{DS} = 12\ V$; $V_{GS} = 0\ V$; $f = 1\ MHz$; $T_j = 25\ ^\circ C$; see Figure 12	-	1565	-	pF
		$V_{DS} = 0\ V$; $V_{GS} = 0\ V$; $f = 1\ MHz$; $T_j = 25\ ^\circ C$	-	1839	-	pF
C_{oss}	output capacitance	$V_{DS} = 12\ V$; $V_{GS} = 0\ V$; $f = 1\ MHz$; $T_j = 25\ ^\circ C$; see Figure 12	-	355	-	pF
C_{rss}	reverse transfer capacitance		-	186	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 12\ V$; $R_L = 0.5\ \Omega$; $V_{GS} = 4.5\ V$; $R_{G(ext)} = 5.6\ \Omega$	-	20	-	ns
t_r	rise time		-	41	-	ns
$t_{d(off)}$	turn-off delay time		-	15	-	ns

Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t _f	fall time	V _{DS} = 12 V; R _L = 0.5 Ω; R _L = 0.5 Ω; V _{GS} = 4.5 V; R _{G(ext)} = 5.6 Ω	-	25	-	ns
Source-drain diode						
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see Figure 14	-	0.89	1.16	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/s; V _{GS} = 0 V;	-	43	-	ns
Q _r	recovered charge	V _{DS} = 30 V	-	15	-	nC

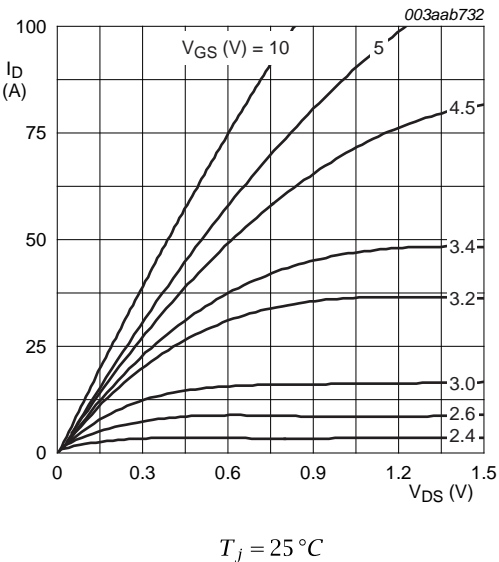


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

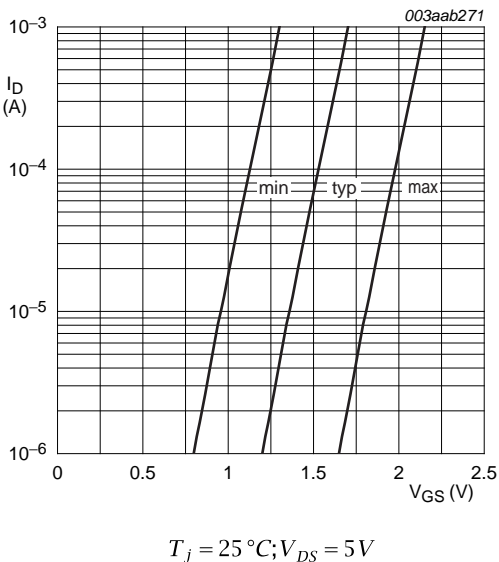
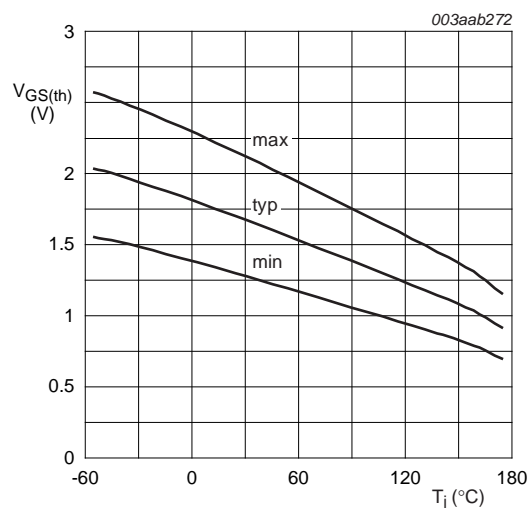
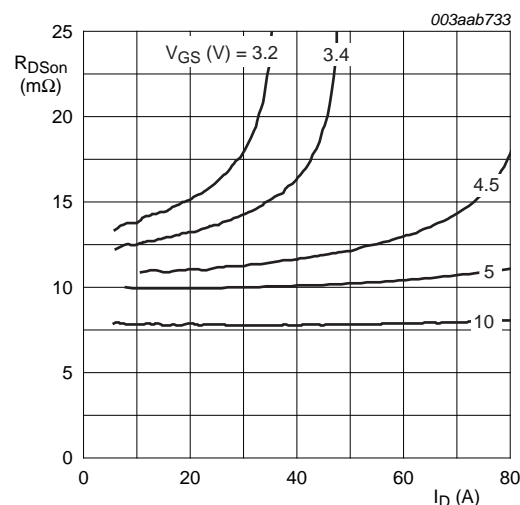


Fig 6. Sub-threshold drain current as a function of gate-source voltage



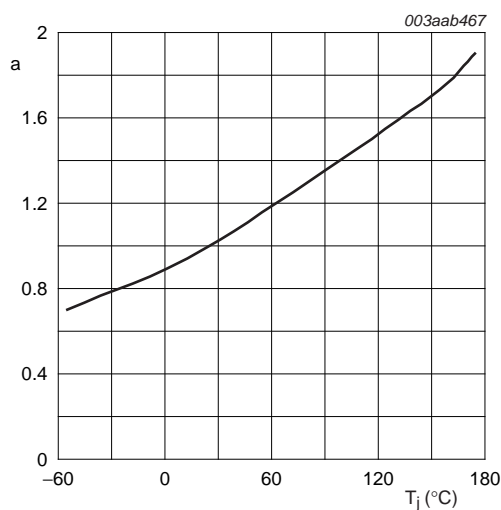
$$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$$

Fig 7. Gate-source threshold voltage as a function of junction temperature



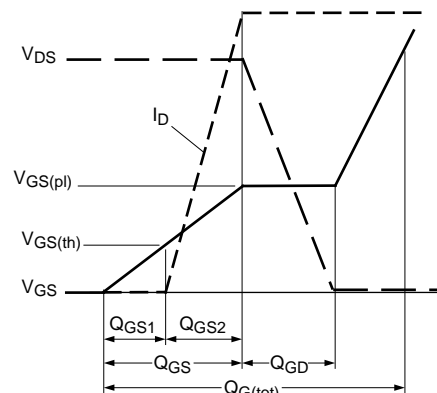
$$T_j = 25^\circ\text{C}$$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



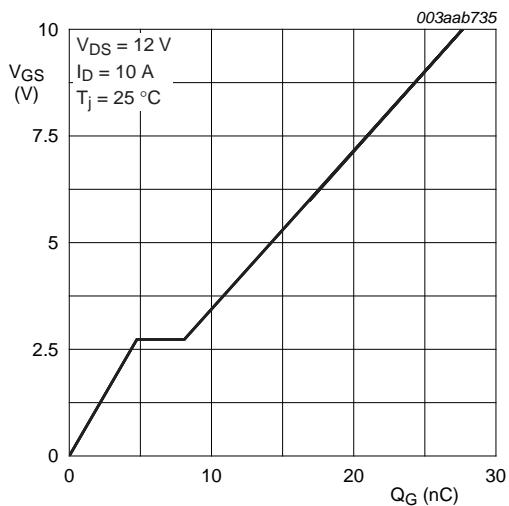
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 9. Normalized drain-source on-state resistance factor as a function of junction temperature



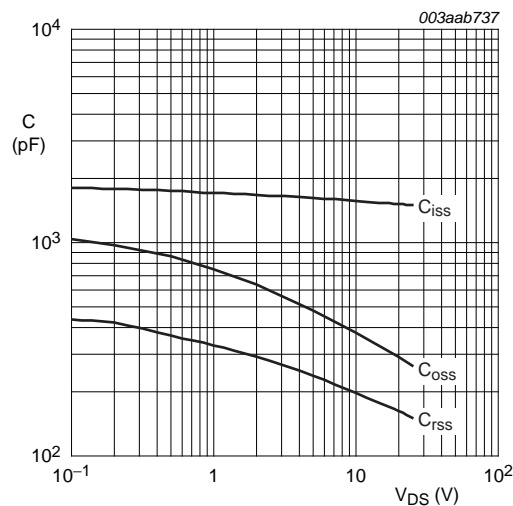
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Fig 10. Gate charge waveform definitions



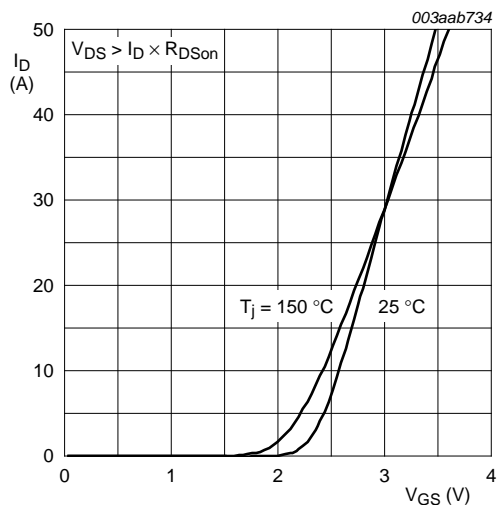
$I_D = 10\text{ A}; V_{DS} = 12\text{ V}$

Fig 11. Gate-source voltage as a function of gate charge; typical values



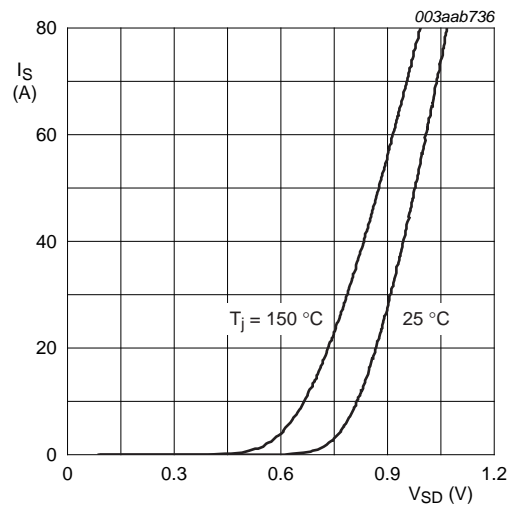
$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$T_J = 25\text{ °C and } 150\text{ °C}; V_{DS} > I_D \times R_{DSon}$

Fig 13. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$T_J = 25\text{ °C and } 150\text{ °C}; V_{GS} = 0\text{ V}$

Fig 14. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (LPAK); 4 leads

SOT669

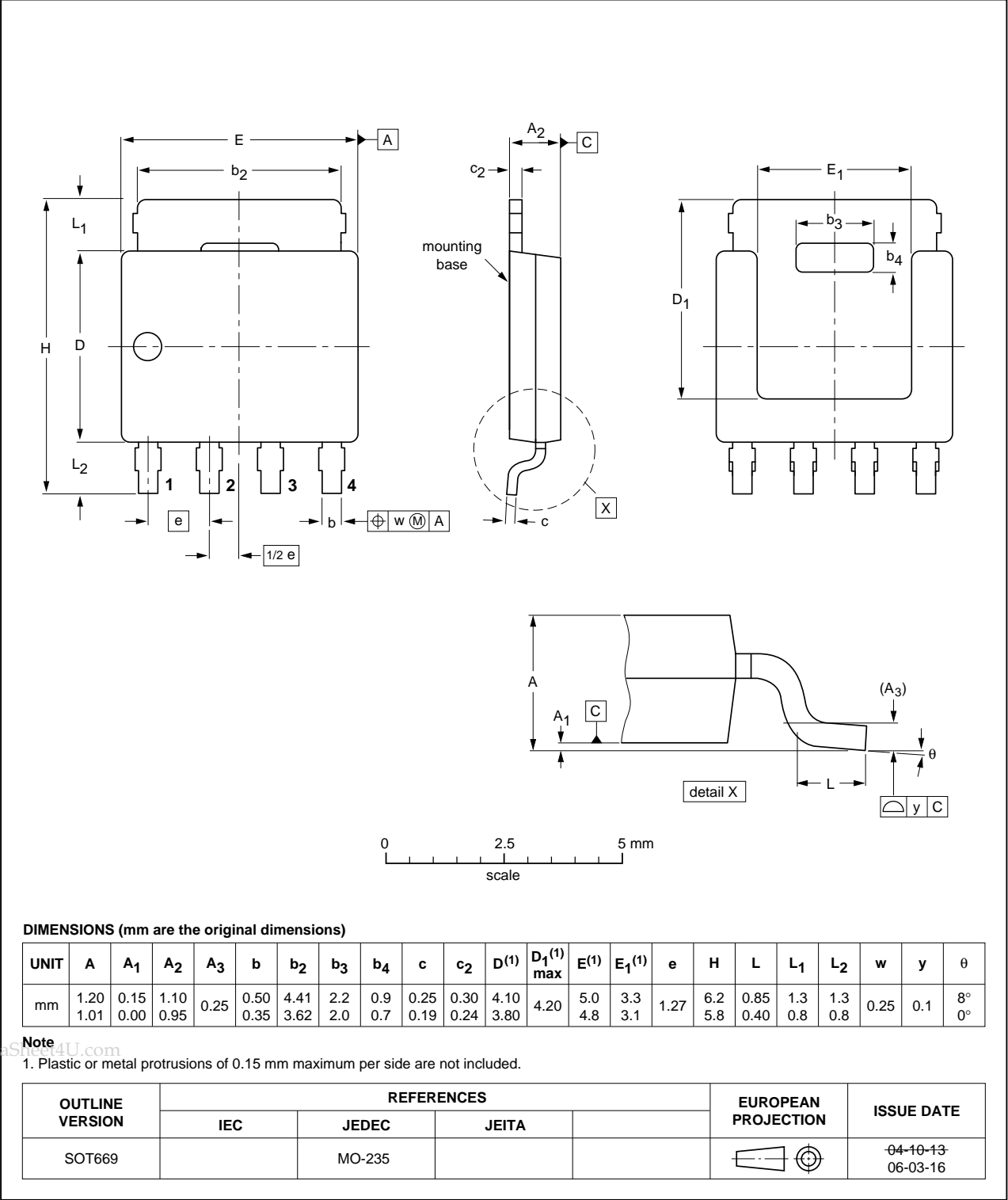


Fig 15. Package outline SOT669 (LPAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PH9030L_1	20080729	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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